TOSHIBA 2SC5355

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

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SWITCHING REGULATOR APPLICATIONS

HIGH VOLTAGE SWITCHING APPLICATIONS

DC-DC CONVERTER APPLICATIONS

Excellent Switching Times

: $t_r = 0.5 \mu s$ (Max.), $t_f = 0.3 \mu s$ (Max.)

High Collector Breakdown Voltage $: V_{CEO} = 400 V$

High DC Current Gain $: h_{FE} = 20 \text{ (Min.)}$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Base Voltage		v_{CBO}	600	V	
Collector-Emitter Voltage		V_{CEO}	400	V	
Emitter-Base Voltage	$V_{ m EBO}$	7	V		
Collector Current	DC	$^{\mathrm{I}}\mathrm{C}$	5	A	
	Pulse	I_{CP}	7		
Base Current	$I_{\mathbf{B}}$	1	A		
Collector Power	$Ta = 25^{\circ}C$	$P_{\mathbf{C}}$	1.5	w	
Dissipation	$Tc = 25^{\circ}C$	1 10	25		
Junction Temperature		T_{j}	150	°C	
Storage Temperature Range		$T_{ m stg}$	-55~150	°C	

0.6MAX. 0.6 ± 0.15 0.95MAX 0.6MAX. 6.8MAX 0.6MAX. 0.6 ± 0.15 0.95MAX. 0.6 ± 0.15 COLLECTOR (HEAT SINK) **EMITTER**

Unit in mm

Weight: 0.36 g

TOSHIBA (A) 2-7B5A (B) 2-7B6A

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARAC	CTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I _{CBO}	$V_{CB} = 480 \text{ V}, I_{E} = 0$	_	_	100	μ A
Emitter Cut-off Current		I _{EBO}	$V_{EB} = 7 \text{ V}, I_{C} = 0$	_	_	10	μ A
Collector-Base Breakdown Voltage			$I_{\mathrm{C}}=1\mathrm{mA},~I_{\mathrm{E}}=0$	600	_	_	V
Collector-Emitter Breakdown Voltage		V (BR) CEO	$I_{\rm C} = 10 {\rm mA}, \; I_{\rm B} = 0$	400	ı	_	V
DC Current Gain			$V_{CE} = 5 V, I_{C} = 1 mA$	12	_		
		h _{FE} (2)	$V_{CE} = 5 V, I_{C} = 0.5 A$	20	_	65	
Collector-Emitter Saturation Voltage		V _{CE} (sat)	$I_C = 2 A, I_B = 0.25 A$	_	_	1.0	V
Base-Emitter Saturation Voltage		V _{BE} (sat)	$I_C = 2 A, I_B = 0.25 A$	_	_	1.3	V
Switching Time Storage T	Turn-on Time	t _{on}	$I_{B1} = 0.25 \text{ A}, V_{CC} = 200 \text{ V}$ $I_{B2} = -0.5 \text{ A}$			0.5	
	Storage Time	$t_{ ext{stg}}$				2.0	μ s
	Fall Time	tf		_	_	0.3	









